

NCCAUS
Junction Technology Group
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Topic: Advances in Implantation & Anneal: 2017

Meeting Date: Friday, July 14, 2017

Time: 1:00 p.m. – 4:30 p.m.

Location: EAG Laboratories
810 Kifer Rd.
Sunnyvale, CA

Co-Chairs: Michael Current, Current Scientific, currentsci@aol.com
John Borland, JOB Technologies, johnborland@aol.com

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AGENDA:

- 1:00-1:30 pm Smartphone Market Driving 7nm & 5nm Node 3-D Devices and Stacked Devices, John Borland, JOB Technologies
- 1:30-2:00 pm Ultra-Shallow Junction Formation on 3D Silicon and Germanium Device Structures by Ion Energy Decoupled Plasma Doping, Y. S. Kim, Lam Research
- 2:00 -2:30 pm Junction formation in Ge by co-implant and pre-heating techniques, Takashi Kuroi, Nissin Ion Implant
- 2:30-3:00 pm Low contact resistance on p-SiGe junctions with Ga implants and laser anneals, Fareen Khaja, Applied Materials
- 3:00-3:30 pm Conversation & Snacks Break:
- 3:30-4:00 pm PLAD advances: Hot n-type implants and Control of sidewall doping, Deven Raj, Applied Materials
- 4:00-4:30 pm Perspectives on low-energy ion (and neutral) implantation, Michael Current, Current Scientific

All presentations will be requested to be posted on the JTG Proceedings webpage approximately 1-2 weeks following the meeting.

➤ ***If you would like to sponsor the JTG July Meeting at SEMICON West, please contact Michael Current, currentsci@aol.com***